**PNP/NPN Epitaxial Planar Silicon Transistors** 



2SB985/2SD1347

# **Large-Current Driving Applications**

# Applcations

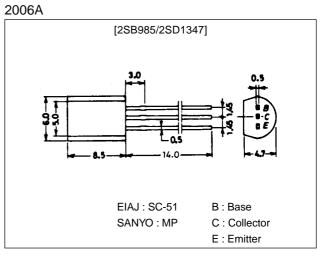
• Power supplies, relay drivers, lamp drivers, electrical equipment.

### **Features**

- · Adoption of FBET, MBIT processes.
- · Low saturation voltage.
- · Large current capacity and wide ASO.

# **Package Dimensions**

unit:mm



():2SB985

# **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

| Parameter                    | Symbol           | Conditions | Ratings     | Unit |
|------------------------------|------------------|------------|-------------|------|
| Collector-to-Base Voltage    | V <sub>CBO</sub> |            | (–)60       | V    |
| Collector-to-Emitter Voltage | VCEO             |            | (–)50       | V    |
| Emitter-to-Base Voltage      | VEBO             |            | (-)6        | V    |
| Collector Current            | IC               |            | (-)3        | A    |
| Collector Current (Pulse)    | I <sub>CP</sub>  |            | (-)6        | A    |
| Collector Dissipation        | PC               |            | 1           | W    |
| Junction Temperature         | Tj               |            | 150         | °C   |
| Storage Temperature          | Tstg             |            | -55 to +150 | °C   |

### Electrical Characteristics at Ta = 25°C

| Parameter                      | Symbol            | Conditions                                       | Ratings |        |        | Unit |
|--------------------------------|-------------------|--|---------|--------|--------|------|
|                                |                   |  | min     | typ    | max    | Unit |
| Collector Cutoff Current       | ICBO              | V <sub>CB</sub> =(-)40V, I <sub>E</sub> =0       |         |        | (–)1.0 | μA   |
| Emitter Cutoff Current         | IEBO              | V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0        |         |        | (–)1.0 | μA   |
| DC Current Gain                | h <sub>FE</sub> 1 | V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)100mA | 100*    |        | 560*   |      |
|                                | h <sub>FE</sub> 2 | V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)3A    | 40      |        |        |      |
| Gain-Bandwidth Product         | fT                | V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)50mA |         | 150    |        | MHz  |
| Common Base Output Capacitance | Cob               | V <sub>CB</sub> =(-)10V, f=1MHz                  |         | 25(39) |        | pF   |

\* : The 2SB985/2SD1347 are classified by 100mA h<sub>FE</sub> as follows :

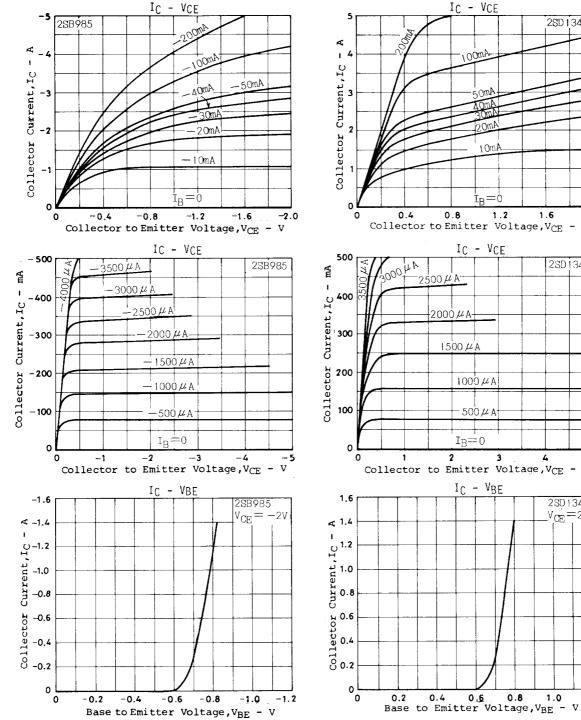
100 R 200 140 S 280 200 T 400 280 U 560

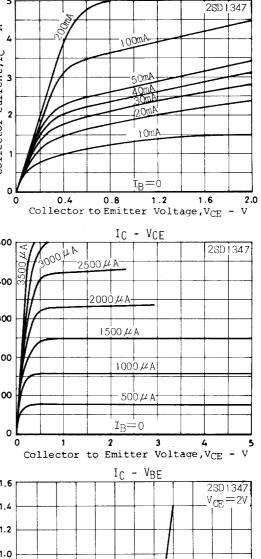
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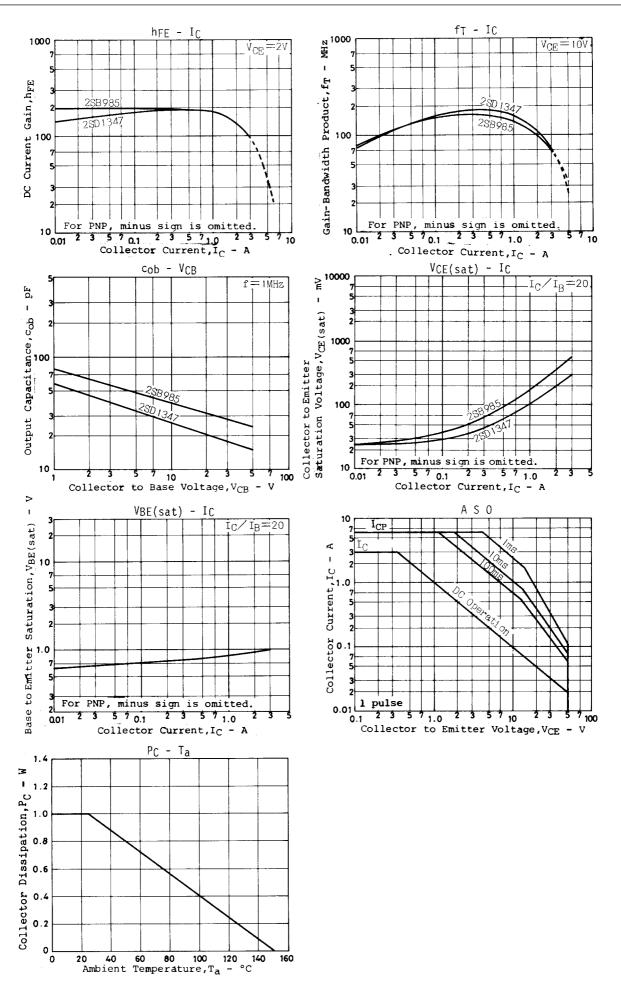
# 2SB985/2SD1347

| Parameter                               | Symbol                | Conditions                                      | Ratings |         |        | Unit |
|---|-----------------------|---|---------|---------|--------|------|
|   | Symbol                |   | min     | typ     | max    | Onit |
| Collector-to-Emitter Saturation Voltage | VCE(sat)              | I <sub>C</sub> =(-)2A, I <sub>B</sub> =(-)100mA |         | 0.19    | 0.5    | V    |
|   |                       |   |         | (-0.35) | (-0.7) | V    |
| Base-to-Emitter Saturation Voltage      | V <sub>BE(sat)</sub>  | I <sub>C</sub> =(-)2A, I <sub>B</sub> =(-)100mA |         | ()0.94  | (–)1.2 | V    |
| Collector-to-Base Breakdown Voltage     | V(BR)CBO              | I <sub>C</sub> =(-)10μA, I <sub>E</sub> =0      | (–)60   |         |        | V    |
| Collector-to-Emitter Breakdown Voltage  | V <sub>(BR)</sub> CEO | I <sub>C</sub> =(−)1mA, R <sub>BE</sub> =∞      | (–)50   |         |        | V    |
| Emitter-to-Base Breakdown Voltage       | V <sub>(BR)EBO</sub>  | I <sub>E</sub> =(–)10μΑ I <sub>C</sub> =0       | (–)6    |         |        | V    |





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